

MMBT2907A

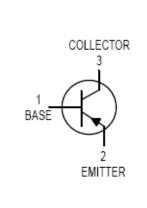
PNP General Purpose Transistor

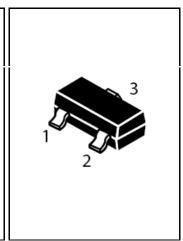
FEATURES

- Ideal for Medium Power Amplification and Switching
- Complementary PNP Type available(MMBT2222A)

MECHANICAL DATA

- Case: SOT-23 Plastic
- Case material: "Green" molding compound, UL flammability classification 94V-0, (No Br. Sb. Cl)
- Lead Free in RoHS 2002/95/EC Compliant





Maximum Ratings @ $T_A = 25^{\circ}C$

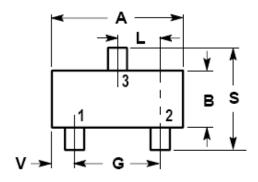
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I _C	-600	mA
Collector Power Dissipation	Pc	250	mW
Thermal Resistance, junction to Ambient	$R_{\theta JA}$	500	°C/W
Junction Temperature	TJ	150	$^{\circ}\mathbb{C}$
Storage Temperature Range	T _{STG}	-55~+150	$^{\circ}\!\mathbb{C}$

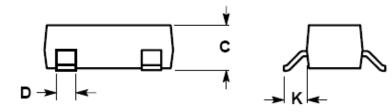
Electrical Characteristics @ T_A = 25 $^{\circ}$ C unless otherwise specified

Characteristic	Test Condition	Symbol	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	I_{C} =-10 μ A, I_{E} =0	V_{CBO}	-60			V
Collector-emitter breakdown voltage	I _C =-10mA,I _B =0	V _{CEO}	-60			V
Emitter-base breakdown voltage	I _E =-10μA,I _C =0	V_{EBO}	-5			V
Collector-base cut-off current	V _{CB} =-50V,I _E =0	I _{CBO}			-20	nA
Emitter-base cut-off current	V_{EB} =-3 V , I_{C} =0	I _{EBO}			-10	nA
Collector-emitter cut-off current	V _{CE} =-30V,V _{BE(off)} =-0.5V	I _{CEX}			-50	nA
	V _{CE} =-10V,I _C =-150mA	h _{FE1}	100		300	
	V_{CE} =-10V, I_{C} =-0.1mA	h _{FE2}	75			
DC current gain	V_{CE} =-10V, I_{C} =-1mA	h _{FE3}	100			
	V _{CE} =-10V,I _C =-10mA	h _{FE4}	100			
	V _{CE} =-10V,I _C =-500mA	h _{FE5}	50			
Collector-emitter saturation voltage	I _C =-150mA,I _B =-15mA	V _{CE} (sat)1			-0.4	V
Collector-entitler saturation voltage	I _C =-500mA,I _B =-50mA	V _{CE} (sat)2			-1.6	V
Page emitter acturation voltage	I _C =-150mA,I _B =-15mA	V _{BE} (sat)1			-1.3	V
Base-emitter saturation voltage	I _C =-500mA,I _B =-50mA	V _{BE} (sat)2			-2.6	V
Transition frequency	V _{CE} =-20V,I _C =-50mA, f=100MHz	f _T	200			MHz
Delay time	V _{CC} =-30V,	T _d			10	nS
Rise time	I _C =-150mA , I _{B1} =-15mA	T _r			25	nS
Storage time	V _{CC} =-6V, I _C =-150mA	Ts			225	nS
Fall time	I _{B1} =-I _{B2} =-15mA	T _f			60	nS

REV.3, Jan - 2013, KSPR11

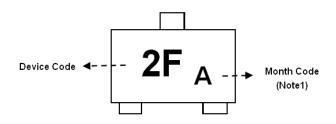
SOT-23 Outline Dimension





Symbol	Dimension In Millimeters						
	Min	Max.					
Α	2.80	3.04					
В	1.20	1.40					
С	0.89	1.11					
D	0.37	0.50					
G	1.78	2.04					
J	0.085	0.177					
K	0.35	0.69					
L	0.89	1.02					
S	2.10	2.64					
V	0.45	0.60					

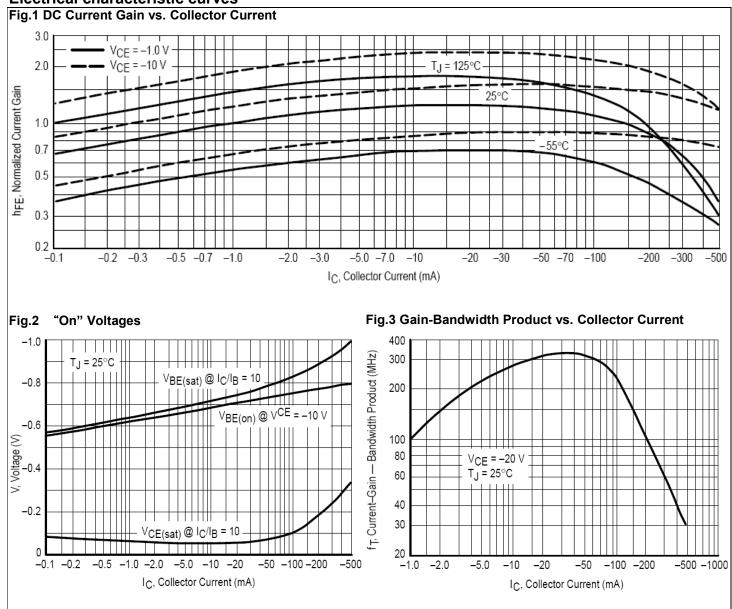
Device Marking:



Note1:

Odd Year	J	0	L	С	K	В	Р	D	M	Е	G	F
Even Year	W	N	Υ	Т	R	Н	Α	ı	U	X	Z	S

Electrical characteristic curves





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